

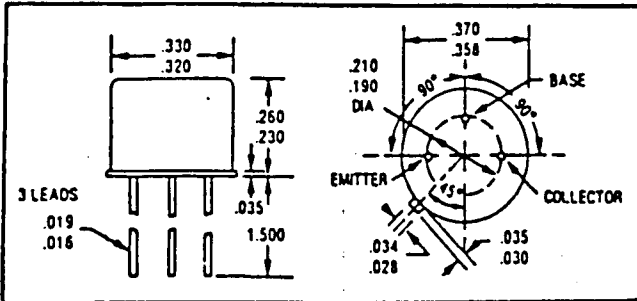
X00144

# SFT6900 3 AMP HIGH VOLTAGE PNP TRANSISTOR 500 VOLTS



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**CASE STYLE W  
JEDEC TO-5**



**FEATURES**

- BV<sub>CEO</sub> TO 400 VOLTS
- LOW SATURATION VOLTAGE
- VERY LOW LEAKAGE
- 200°C OPERATING, GOLD EUTECTIC DIE ATTACH
- HIGH LINEAR GAIN FROM 1 mA TO 1 AMP
- DESIGNED FOR COMPLEMENTARY USE WITH SFT6800 (NPN) AND 2N5663 SERIES

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage $R_{BE} = 1 \text{ K Ohms}$	$V_{CEO}$ $V_{CER}$	400 500	Volts
Collector - Base Voltage	$V_{CBO}$	500	Volts
Emitter - Base Voltage	$V_{EBO}$	9	Volts
Collector Current	$I_C$	3	Amps
Base Current	$I_B$	1	Amps
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 °C	$P_D$	5 160	Watts mW/°C
Operating and Storage Temperature	$T_j, T_{stg}$	-65 to +200	°C

**THERMAL CHARACTERISTICS**

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6	°C/W

**ELECTRICAL CHARACTERISTICS**

Characteristics	Symbol	Min.	Max.	Unit
Collector - Emitter Breakdown Voltage* $(I_C = 50 \text{ mA dc}, T_p = 300 \text{ usec})$ $(I_C = 100 \text{ uA dc}, R_{BE} = 1 \text{ K ohms})$	$BV_{CEO}$ $BV_{CER}$	400 500		Vdc
Collector - Base Breakdown Voltage $(I_C = 100 \text{ uA dc})$	$BV_{CBO}$	500		Vdc
Emitter - Base Breakdown Voltage $(I_E = 20 \text{ uA dc})$	$BV_{EBO}$	9		Vdc

# ELECTRICAL CHARACTERISTICS

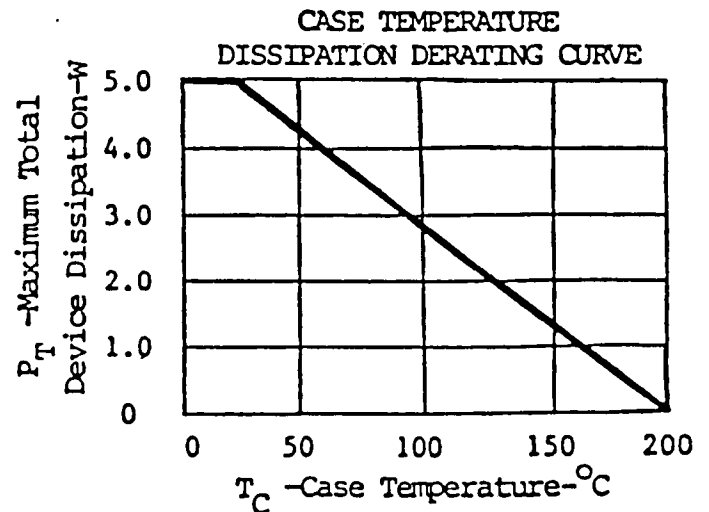
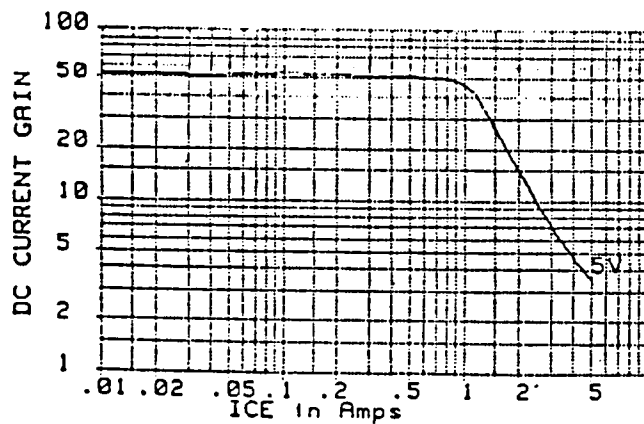
Characteristics	Symbol	Min.	Max.	Unit
Collector Cutoff Current ( $V_{CE} = 400 \text{ Vdc}, V_{BE} = -1.5 \text{ Vdc}$ )	$I_{CEV}$		200	n Adc
Collector Cutoff Current ( $V_{CB} = 400 \text{ Vdc}$ )	$I_{CBO}$		200	n Adc
Emitter Cutoff Current ( $V_{EB} = 6.0 \text{ Vdc}$ )	$I_{EBO}$		200	n Adc
DC Current Gain* ( $I_C = 50 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 500 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 1.0 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$ )	$h_{FE}$	40 35 25	200 250	
Collector - Emitter Saturation Voltage* ( $I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$ ) ( $I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$ )	$V_{CE (SAT)}$		400 500	m Vdc.
Base - Emitter Saturation Voltage* ( $I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$ ) ( $I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$ )	$V_{BE (SAT)}$		0.9 1.0	Vdc
Current - Gain - Bandwith Product ( $I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 20 \text{ MHz}$ )	$f_T$	25		MHz
Output Capacitance ( $V_{CB} = 30 \text{ Vdc}, I_E = 0.1 = 1.0 \text{ Hz}$ )	$C_{ob}$		150	pf

## SWITCHING TIMES

Delay Time	( $I_C = 1.0 \text{ Adc},$ $V_{CC} = 150 \text{ Vdc},$ $I_{B1} = I_{B2} = 100 \text{ mAdc}$ )	$t_d$			
Rise Time		$t_r$ +		450	ns
Storage Time		$t_s$			
Fall Time		$t_f$ +		1.8	us

\*Pulse Test: Pulse width = 300 us, DutyCycle = 2%

## TYPICAL OPERATING CURVES



**SSDI** SOLID STATE DEVICES, INC.